TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HC375AP,TC74HC375AF,TC74HC375AFN

4-Bit D Type Latch

The TC74HC375A is a high speed CMOS D-TYPE LATCH fabricated with silicon gate C^2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

It contains two groups of 2-bit latches controlled by an enable input (G1·2 or G3·4) and each group can be used in different circuits

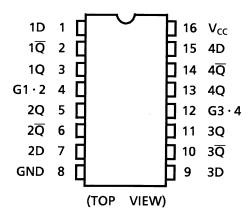
Data applied to the data inputs are transferred to the Q and \overline{Q} outputs whin the enable inputs is high. When the enable input is low, the outputs are not affected.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

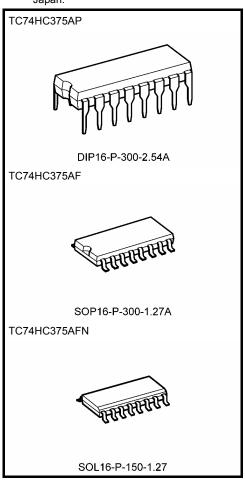
Features

- High speed: $t_{pd} = 14 \text{ ns (typ.)}$ at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 4 \mu A$ (max) at $T_a = 25$ °C
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Output drive capability: 10 LSTTL loads
- Symmetrical output impedance: | I_{OH}| = I_{OL} = 4 mA (min)
- Balanced propagation delays: t_{pLH} ≃ t_{pHL}
- Wide operating voltage range: VCC (opr) = 2 to 6 V
- Pin and function compatible with 74LS375

Pin Assignment



Note: xxxFN (JEDEC SOP) is not available in Japan.



Weight

DIP16-P-300-2.54A : 1.00 g (typ.) SOP16-P-300-1.27A : 0.18 g (typ.) SOL16-P-150-1.27 : 0.13 g (typ.)

IEC Logic Symbol

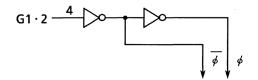
1D (1)	1D	(3) 1Q
G1 · 2 (4)	C1	(2) 1Q (5) 1Q
(7)	C2	(5) 2Q
2D (7) 3D (9)	2D	(6) 2Q (11) 2Q
3D (3)	3D	(11) 3Q
G3 · 4 (12)	C3	(11) 3Q (10) 3Q
(15)	C4	$\frac{(13)}{(14)}$ 4Q
4D (13)	4D	$\frac{(14)}{4\overline{Q}}$

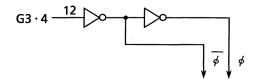
Truth Table

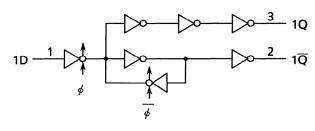
Inp	uts	Out	puts	Function
D	G	Q	IQ	Function
L	Н	L	Н	_
Н	Н	Н	L	_
Х	L	Qn	- Qn	Latch

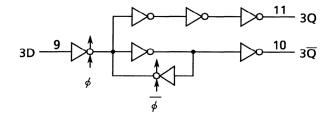
X: Don't care

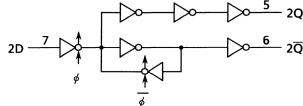
System Diagram

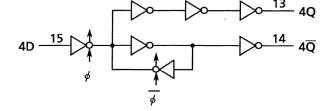














Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	–0.5 to 7	V
DC input voltage	V _{IN}	-0.5 to V _{CC} + 0.5	V
DC output voltage	V _{OUT}	−0.5 to V _{CC} + 0.5	٧
Input diode current	I _{IK}	±20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C shall be applied until 300 mW.

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2 to 6	V
Input voltage	V _{IN}	0 to V _{CC}	٧
Output voltage	V _{OUT}	0 to V _{CC}	٧
Operating temperature	T _{opr}	−40 to 85	°C
		0 to 1000 (V _{CC} = 2.0 V)	
Input rise and fall time	t _r , t _f	0 to 500 (V _{CC} = 4.5 V)	ns
		0 to 400 (V _{CC} = 6.0 V)	

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

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Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition			Ta = 25°C		Ta = -40 to 85°C		Unit	
				V _{CC} (V)	Min	Тур.	Max	Min	Max	
				2.0	1.50	_	_	1.50	_	
High-level input voltage	V_{IH}		_	4.5	3.15	_	_	3.15	_	V
o de la companya de l				6.0	4.20	—	_	4.20	_	
				2.0	_	_	0.50	_	0.50	
Low-level input voltage	V_{IL}		_	4.5	_	_	1.35		1.35	V
				6.0	_	_	1.80	_	1.80	
				2.0	1.9	2.0		1.9	_	
l		V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -20 \mu A$	4.5	4.4	4.5	_	4.4	_	
High-level output voltage	V_{OH}			6.0	5.9	6.0	_	5.9	_	V
			$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31		4.13	_	
			$I_{OH} = -5.2 \text{ mA}$	6.0	5.68	5.80	_	5.63	_	
				2.0	_	0.0	0.1		0.1	
			$I_{OL} = 20 \mu A$	4.5	_	0.0	0.1		0.1	
Low-level output voltage	V_{OL}	V _{IN} = V _{IH} or V _{IL}		6.0	_	0.0	0.1	_	0.1	V
			I _{OL} = 4 mA	4.5	_	0.17	0.26	_	0.33	
			I _{OL} = 5.2 mA	6.0		0.18	0.26	_	0.33	
Input leakage current	I _{IN}	V _{IN} = V _{CC} or GND		6.0			±0.1		±1.0	μА
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or	GND	6.0	_	_	4.0	_	40.0	μА

Timing Requirements (input: $t_r = t_f = 6$ ns)

Characteristics	Symbol	Test Condition	Test Condition			Ta = -40 to 85°C	Unit
			V _{CC} (V)	Тур.	Limit	Limit	
Minimum nulae width			2.0	_	75	95	
Minimum pulse width	t _{W (H)}	_	4.5	_	15	19	ns
(G)			6.0	_	13	16	
	t _s		2.0	_	75	95	
Minimum set-up time		_	4.5	_	15	19	ns
			6.0	_	13	16	
			2.0	_	0	0	
Minimum hold time	t _h	_	4.5	_	0	0	ns
			6.0	_	0	0	



AC Characteristics (C_L = 15 pF, V_{CC} = 5 V, Ta = 25°C, input: t_r = t_f = 6 ns)

Characteristics	Symbol	Test Condition		Тур.	Max	Unit
Output transition time	t _{TLH}			4	8	ns
Output transition time	t_{THL}					113
Propagation delay time	t_{pLH}			14	20	20
$(D-Q, \overline{Q})$	t_{pHL}	_	_	14	20	ns
Propagation delay time	t _{pLH}			12	20	20
$(G-Q, \overline{Q})$	t_{pHL}			13	20	ns

AC Characteristics ($C_L = 50 \text{ pF}$, input: $t_r = t_f = 6 \text{ ns}$)

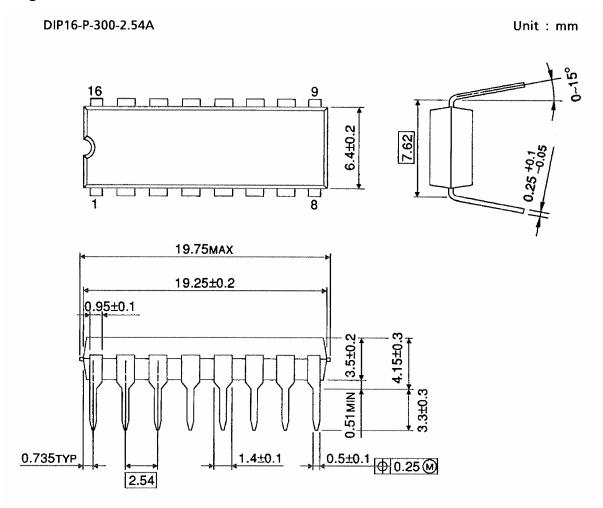
Characteristics Sy	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit
	,		V _{CC} (V)	Min	Тур.	Max	Min	Max	
	4		2.0	_	30	75	_	95	
Output transition time	t _{TLH}	_	4.5	_	8	15	_	19	ns
	t _{THL}		6.0	_	7	13	_	16	
Propagation delay	4		2.0	_	60	120	_	150	
time	t _{pLH}	_	4.5	_	17	24	_	30	ns
$(D-Q, \overline{Q})$	t _{pHL}		6.0	_	15	20	_	26	
Propagation delay	4		2.0	_	56	120	_	150	
time	t _{pLH}	_	4.5	_	16	24	_	30	ns
$(G-Q, \overline{Q})$	t _{pHL}		6.0	_	14	20	_	26	
Input capacitance	C _{IN}	_		_	5	10	_	10	pF
Power dissipation capacitance	C _{PD} (Note)	_		_	55	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}$$
 (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4$ (per latch)

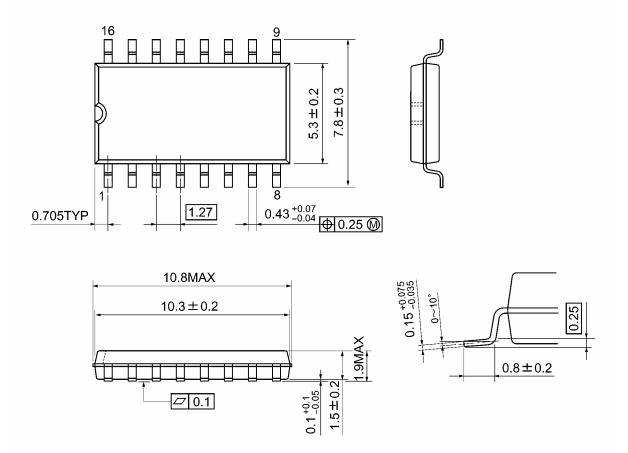
Package Dimensions



Weight: 1.00 g (typ.)

Package Dimensions

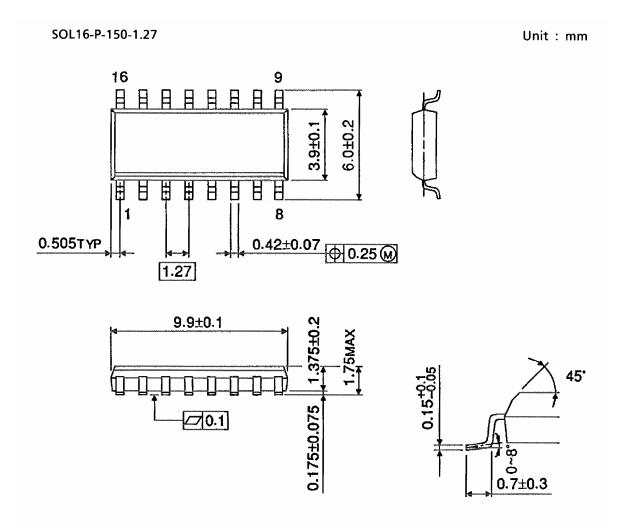
SOP16-P-300-1.27A Unit: mm



Weight: 0.18 g (typ.)



Package Dimensions (Note)



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Note: This package is not available in Japan.

Weight: 0.13 g (typ.)

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20070701-EN GENERAL

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